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cont

an active element provided on a semiconductor substrate, said active element including at least two diffusion layers and a gate electrode;

a first metal wiring layer formed on the active element;

a plurality of other metal wiring layers above said active element; and

a plurality of interlayer insulating films each being provided between a pair of said metal wiring layers,

wherein each interlayer insulating film has a multilayer structure including at least a spin-on-glass film sandwiched between insulating films formed of a silicon nitride film or a silicon oxide film;

further wherein the film formed of spin-on-glass in the interlayer insulating film being formed to a minimum thickness necessary for compensating a level difference of one of said metal wiring layers;

a pad metal for an electrode pad, said pad metal being provided on said interlayer insulating film.

REMARKS

Reconsideration of this application is respectfully requested. The foregoing amendments to claim 25 merely serve to correct a grammatical error therein.

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page(s) is captioned "Version With Markings To Show Changes Made."

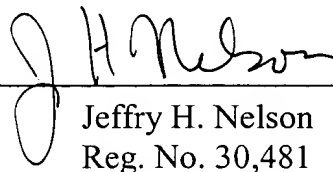
TOYOSAWA et al
Serial No. 09/598,169

All claims are in good condition for allowance. If any small matter remains outstanding, the Examiner is requested to telephone applicants' attorney. Prompt reconsideration and allowance of this application would be appreciated. If any additional fees are required with the filing of this amendment, please charge the account of Nixon & Vanderhye P.C., account No. 14-1140.

Respectfully submitted,

NIXON & VANDERHYE P.C.

By: _____


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